

# photodiodes



## Silicon PIN Photodiodes and Modules

- Broad Range of Photosensitive Areas
- Low Operating Voltage
- Hermetically Sealed Packages

### Si PINs—Window and Lightpipe Packages, Fast Response—400 nm to 1100 nm

#### Technical Specification

Part Number	Standard Package	Photo Sens. Diam. mm	Resp. @830 nm A/W	Dark Curr. Id nA	Spect. Noise Curr. Dens. In (fA/√Hz)	Cap. @100 kHz Cd (pF)	Resp. Time tr (ns)	NEP @ 830 nm fW/√Hz	Bias Volt for These Specs V
C30971E	TO-18	0.5	0.5	10	57	1.6	0.5	113	100
C30971EL	TO-18 Lightpipe	0.25	0.5	10	57	1.6	0.5	113	100

Test conditions: T = 22°C

### Si PINs—Large Area, Fast Response—400 nm to 1100 nm

#### Technical Specification

Part Number	Standard Package	Photo Sens. Diam. mm	Resp. @900 nm A/W	Dark Curr. Id nA	Spect. Noise Curr. Dens. In (fA/√Hz)	Cap. @100 kHz Cd (pF)	Resp. Time tr (ns)	NEP @ 900 nm fW/√Hz	Bias Volt for These Specs V
FFD-100	TO-5	2.5	0.58	2	25	8.5	3.5	44	15
FFD-200	TO-8	5.1	0.58	4	36	30	5	62	15

Test conditions: T = 22°C

### Si PINs—Quadrant—220 nm to 1100 nm

#### Technical Specification

Part Number	Standard Package	Photo Sens. Diam. total mm	Resp. @900 nm A/W	Dark Curr. Id nA	Spect. Noise Curr. Dens. In (fA/√Hz)	Cap. @100 kHz Cd (pF)	Resp. Time tr (ns)	NEP @ 900 nm fW/√Hz	Bias Volt for These Specs V
C30845E	TO-5	8	0.6	7	47	8	6	79	45
UV-140BQ-4	TO-5	1.3x1.3 (x4)	0.58	—	4	34	<1 μsec	7	0
YAG-444-4A	Custom	11.4	0.4 @1.06 μm	40	118	9	25	295	180

Test conditions: T = 22°C

### Si PINs—Standard N-Type—400 nm to 1100 nm

#### Technical Specification

Part Number	Standard Package	Photo Sens. Diam. mm	Resp. @900 nm A/W	Dark Curr. Id nA	Spect. Noise Curr. Dens. In (fA/√Hz)	Cap. @100 kHz Cd (pF)	Resp. Time tr (ns)	NEP @ 900 nm fW/√Hz	Bias Volt for These Specs V
C30807E	TO-18	1	0.6	1	18	2.5	3	30	45
C30808E	TO-5	2.5	0.6	3	31	6	5	52	45
C30822E	TO-8	5	0.6	5	40	17	7	67	45
C30809E	TO-8	8	0.6	7	47	35	10	79	45
C30810E	Custom	11.4	0.6	30	98	70	12	163	45

Test conditions: T = 22°C